

4V Drive Nch+Nch MOSFET

SP8K31

●Structure

Silicon N-channel
MOSFET

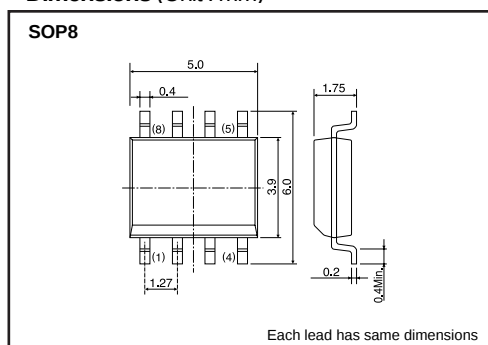
●Features

- 1) Built-in G-S Protection Diode.
- 2) Small surface Mount Package (SOP8).

●Applications

Switching

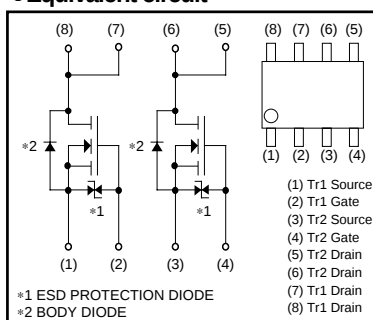
●Dimensions (Unit : mm)



●Packaging dimensions

Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
SP8K31		○

●Equivalent circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

●Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	± 20	V
Drain current	Continuous	I_D	± 3.5 A
	Pulsed	I_{DP} *1	± 14 A
Source current (Body diode)	Continuous	I_S	1.0 A
	Pulsed	I_{SP} *1	14 A
Total power dissipation	P_D *2	2.0	W
Channel temperature	T_{ch}	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board.

Transistor

●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	—	—	±10	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	60	—	—	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	—	2.5	V	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state resistance	R _{DS (on)} *	—	85	120	mΩ	I _D = 3.5A, V _{GS} = 10V
		—	100	140	mΩ	I _D = 3.5A, V _{GS} = 4.5V
		—	105	150	mΩ	I _D = 3.5A, V _{GS} = 4.0V
Forward transfer admittance	Y _{fs} *	2.5	—	—	S	V _{DS} = 10V, I _D = 3.5A
Input capacitance	C _{iss}	—	250	—	pF	V _{DS} = 10V
Output capacitance	C _{oss}	—	60	—	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	—	30	—	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	—	7	—	ns	V _{DD} ≐ 30V
Rise time	t _r *	—	14	—	ns	I _D = 1.8A
Turn-off delay time	t _{d (off)} *	—	25	—	ns	V _{GS} = 10V
Fall time	t _f *	—	7	—	ns	R _L = 17Ω
Total gate charge	Q _g *	—	3.7	5.2	nC	R _G =10Ω
Gate-source charge	Q _{gs} *	—	1.2	—	nC	V _{DD} ≐ 30V, V _{GS} = 5V
Gate-drain charge	Q _{gd} *	—	1.2	—	nC	I _D = 3.5A
						R _L = 8.6Ω, R _G = 10Ω

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	—	—	1.2	V	I _S =3.5A, V _{GS} =0V

*Pulsed

Transistor

●Electrical characteristic curves

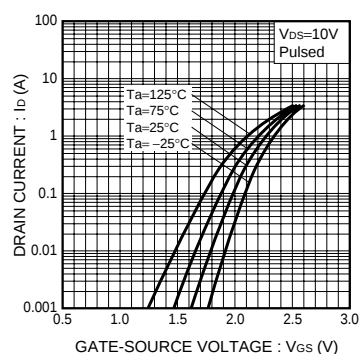


Fig.1 Typical Transfer Characteristics

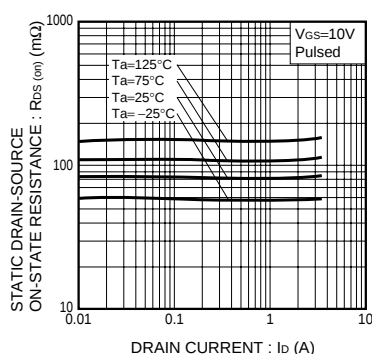
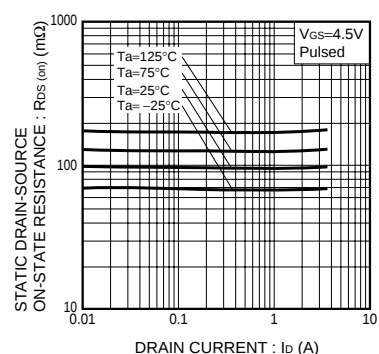
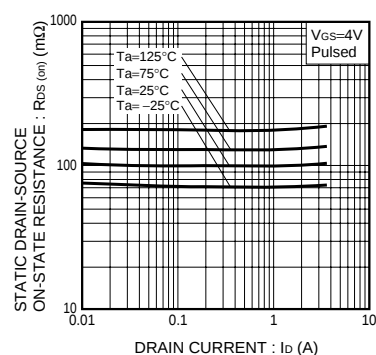
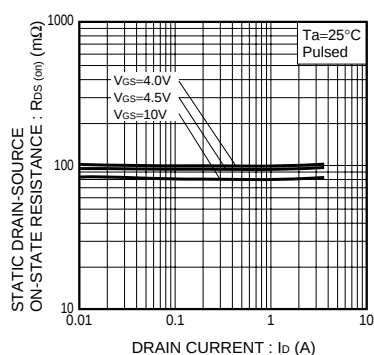
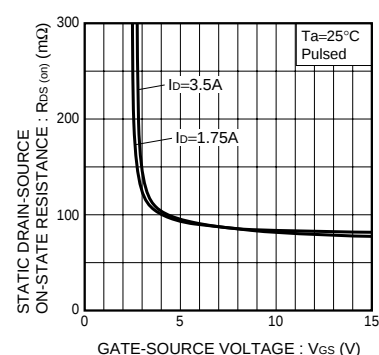
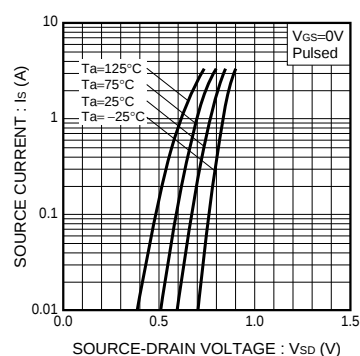
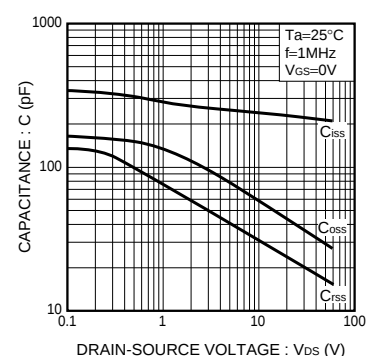
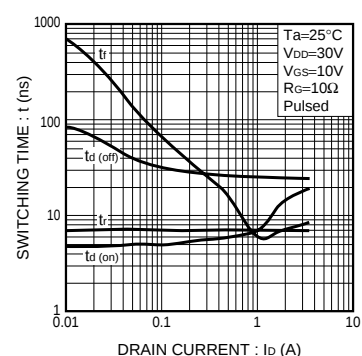
Fig.2 Static Drain-Source
On-State Resistance
vs. Drain Current(I)Fig.3 Static Drain-Source
On-State Resistance
vs. Drain Current(II)Fig.4 Static Drain-Source
On-State Resistance
vs. Drain Current(III)Fig.5 Static Drain-Source
On-State Resistance
vs. Drain Current(IV)Fig.6 Static Drain-Source
On-State Resistance vs.
Gate-Source VoltageFig.7 Source Current vs.
Source-Drain VoltageFig.8 Typical Capacitance
vs. Drain-Source Voltage

Fig.9 Switching Characteristics

Transistor

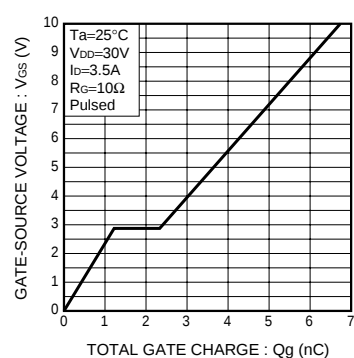


Fig.10 Dynamic Input Characteristics

●Measurement circuits

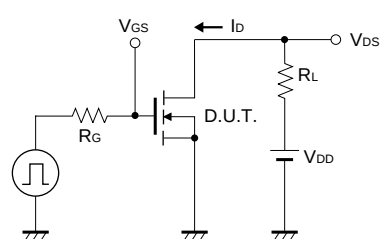


Fig.11 Switching Time Test Circuit

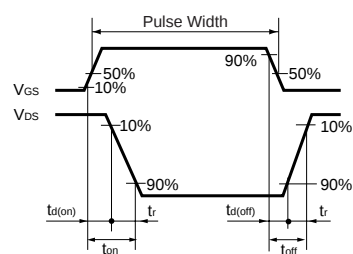


Fig.12 Switching Time Waveforms

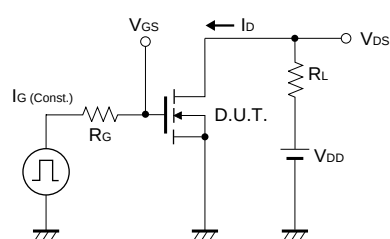


Fig.13 Gate Charge Test Circuit

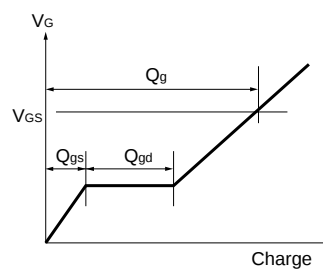


Fig.14 Gate Charge Waveform

Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the product described in this document are for reference only. Upon actual use, therefore, please request that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or otherwise dispose of the same, no express or implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

It is our top priority to supply products with the utmost quality and reliability. However, there is always a chance of failure due to unexpected factors. Therefore, please take into account the derating characteristics and allow for sufficient safety features, such as extra margin, anti-flammability, and fail-safe measures when designing in order to prevent possible accidents that may result in bodily harm or fire caused by component failure. ROHM cannot be held responsible for any damages arising from the use of the products under conditions out of the range of the specifications or due to non-compliance with the NOTES specified in this catalog.

Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact your nearest sales office.

ROHM Customer Support System

THE AMERICAS / EUROPE / ASIA / JAPAN

www.rohm.com

Contact us : webmaster@rohm.co.jp



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331